

form a first metal element added region and a second metal added region;

crystallizing the amorphous semiconductor film so that a crystal growth proceeds in a crystal growth direction parallel to the insulating surface from the first metal element added region and a second metal element added region thereby to form a first crystalline portion and a second crystalline portion, respectively, in a crystalline semiconductor film;

*B' and* patterning the crystalline semiconductor film to form at least a crystalline semiconductor island using only the first crystalline portion while the second crystalline portion is not used to form the crystalline semiconductor island,

wherein carriers move in the crystalline semiconductor island in a carrier moving direction identical with the crystal growth direction,

wherein the metal element added region is located apart from the crystalline semiconductor island by a distance,

wherein the metal element added region has a length extending longer from an end portion of the crystalline semiconductor island in a longitudinal direction of the metal element added region.